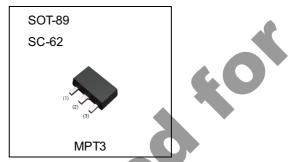


Middle Power Transistors (80V / 1.5A)

Parameter	Value
V _{CEO}	80V
I _C	1.5A

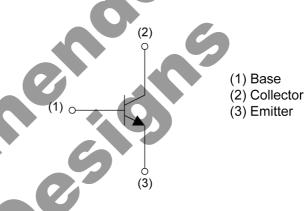
Outline



Features

- 1)Low saturation voltage,typically V_{CE(sat)}=300mV(Max.) (I_C/I_B=500mA/25mA)
- 2)High speed switching

•Inner circuit



Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SCR554P	SOT-89 (MPT3)	4540	T100	180	12	1000	NH

• Absolute maximum ratings ($T_a = 25$ °C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I _C	1.5	Α
Collector current		3	Α
Douge discination	P _D *2	0.5	W
Power dissipation	P _D *3	2.0	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

● Electrical characteristics (T_a = 25°C)

('a	/					
Parameter	Symbol	Conditions	Values		Unit	
r al al lietei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector-base breakdown voltage	BV _{CBO}	Ι _C = 100μΑ	80	S	ı	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	80	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 100μA	6	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 80V	_	1	1.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	1.0	μA
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 500$ mA, $I_B = 25$ mA	-	100	300	mV
DC current gain	h _{FE}	$V_{CE} = 3V, I_{C} = 100 \text{mA}$	120	-	390	-
Transition frequency	f⊤	$V_{CE} = 10V$, $I_{E} = -200$ mA, f = 100MHz	-	300	-	MHz
Output capacitance	C _{ob}	$V_{CB} = 10V$, $I_E = 0A$, $f = 1MHz$	-	10	1	pF
Turn-On time	t _{on}	I _C = 700mA, I _{B1} = 70mA,	-	50	-	ns
Storage time	t _{stg}	$I_{B2} = -70 \text{mA},$ $V_{CC} \simeq 10 \text{V},$	-	600	-	ns
Fall time	t _f	$R_L = 15\Omega$ See test circuit	-	60	-	ns

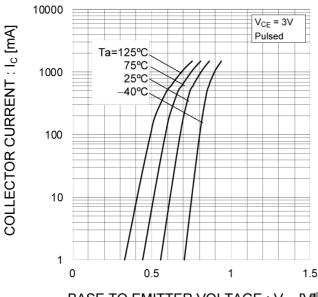
^{*1} Pw=10ms, Single Pulse

^{*2} Each terminal mounted on a reference land.

^{*3} Mounted on a ceramic board.(40×40×0.7mm)

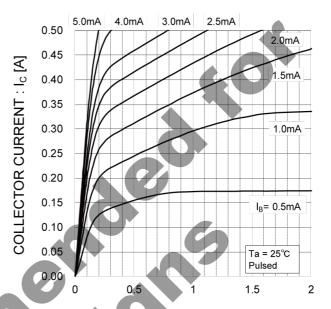
● Electrical characteristic curves(T_a = 25°C)

Fig.1 Ground Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE: VBE [V]

Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

Fig.3 DC Current Gain vs. Collector Current (I)

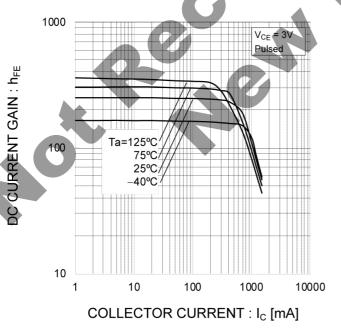
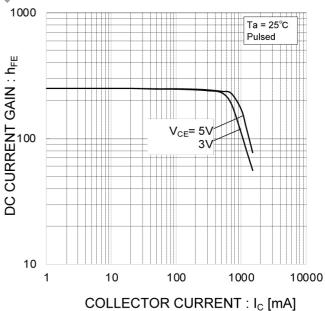


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

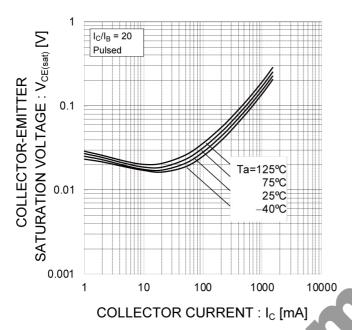


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

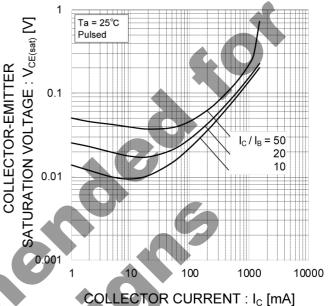


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

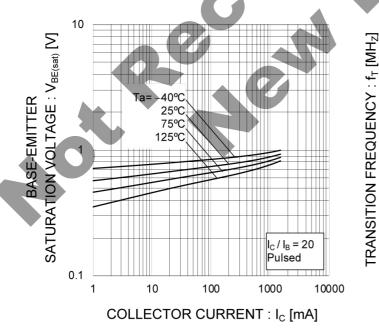
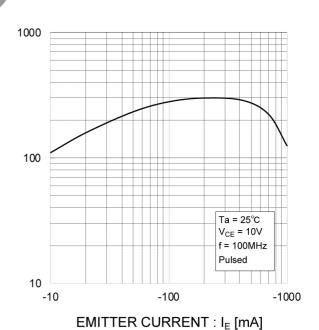


Fig.8 Gain Bandwidth Product vs.
Emitter Current



● Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter Input Capacitance vs.
Emitter-Base Voltage
Collector Output Capacitance vs.
Collector-Base Voltage

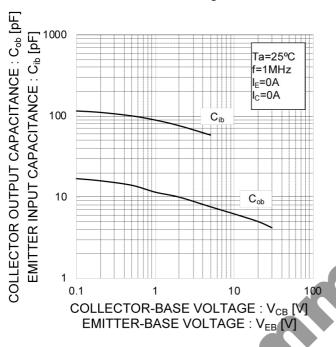
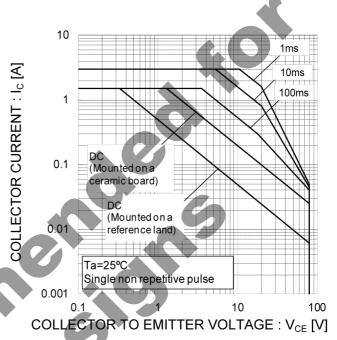
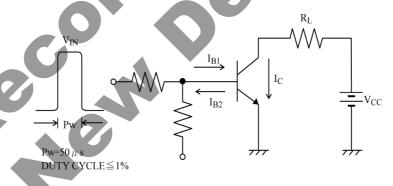
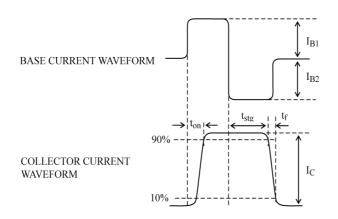


Fig.10 Safe Operating Area

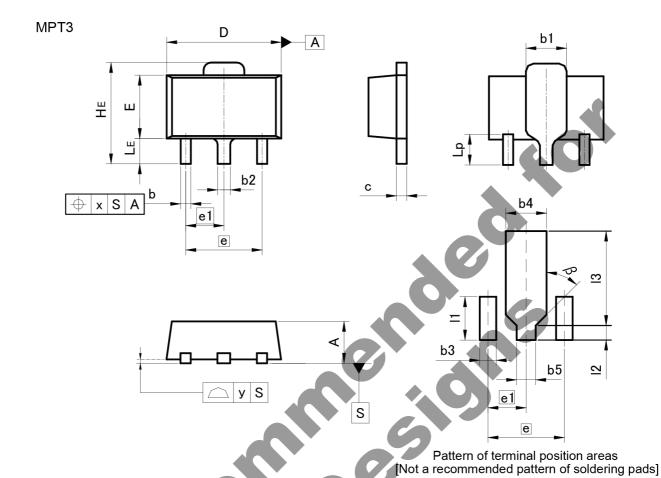


SWITCHING TIME TEST CIRCUIT





Dimensions



DIM	MILIMI	ETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
Α	1.40	1.50	0.055	0.059
b	0.30	0.50	0.012	0.020
b1	1.50	1.70	0.059	0.067
b2	0.40	0.60	0.016	0.024
С	0.35	0.50	0.014	0.020
D	4.40	4.70	0.173	0.185
E	2.40	2.70	0.094	0.106
е	3.0	00	0.1	18
e1	1.5	50	0.0	59
HE	3.70	4.30	0.146	0.169
LE	0.80	1.20	0.031	0.047
Lp	1.01	1.41	0.040	0.056
Х	-	0.15	-	0.006
У	_	0.10	_	0.004

D114	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b3	-	0.65	-	0.026	
b4	1	1.70	ı	0.067	
b5	ı	0.75	ı	0.030	
l1	-	1.71	ı	0.067	
12	ı	0.58	ı	0.023	
13	-	3.72	-	0.146	
R	45°		45	0	

Dimension in mm/inches

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